

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSIII)

# 2SK2608

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS

SWITCHING REGULATOR APPLICATIONS

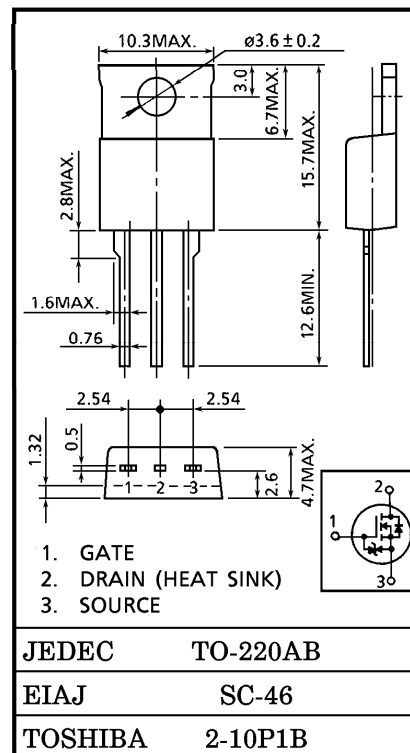
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 3.73 \Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 2.6 S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 100 \mu A$  (Max.) ( $V_{DS} = 720 V$ )
- Enhancement-Mode :  $V_{th} = 2.0 \sim 4.0 V$   
( $V_{DS} = 10 V, I_D = 1 mA$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	900	V
Drain-Gate Voltage ( $R_{GS} = 20 k\Omega$ )	$V_{DGR}$	900	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Drain Current	DC	$I_D$	3 A
	Pulse	$I_{DP}$	9 A
Drain Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	100	W
Single Pulse Avalanche Energy**	$E_{AS}$	295	mJ
Avalanche Current	$I_{AR}$	3	A
Repetitive Avalanche Energy*	$E_{AR}$	10.0	mJ
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ C$



THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.25	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C/W$

Note ;

\* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

\*\*  $V_{DD} = 90 V, T_{ch} = 25^\circ C$  (initial),  $L = 60.0 mH, R_G = 25 \Omega, I_{AR} = 3 A$

**This transistor is an electrostatic sensitive device.**

**Please handle with caution.**

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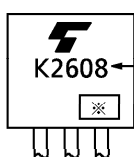
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	—	—	±10	μA	
Gate-Source Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V	±30	—	—	V	
Drain Cut-off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V	—	—	100	μA	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	900	—	—	V	
Gate Threshold Voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	—	4.0	V	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A	—	3.73	4.3	Ω	
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 1.5 A	0.65	2.6	—	S	
Input Capacitance	C <sub>iSS</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	750	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>		—	10	—		
Output Capacitance	C <sub>oss</sub>		—	70	—		
Switching Time	Rise Time	t <sub>r</sub>		—	15	—	ns
	Turn-on Time	t <sub>on</sub>		—	55	—	
	Fall Time	t <sub>f</sub>		—	30	—	
	Turn-off Time	t <sub>off</sub>		V <sub>IN</sub> : t <sub>r</sub> , t <sub>f</sub> < 5 ns, Duty ≤ 1%, t <sub>w</sub> = 10 μs	—	110	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q <sub>g</sub>	V <sub>DD</sub> ≐ 400 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A	—	25	—	nC	
Gate-Source Charge	Q <sub>gs</sub>		—	13	—		
Gate-Drain (“Miller”) Charge	Q <sub>gd</sub>		—	12	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I <sub>DR</sub>	—	—	—	3	A
Pulse Drain Reverse Current	I <sub>DRP</sub>	—	—	—	9	A
Diode Forward Voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 3 A, V <sub>GS</sub> = 0 V	—	—	-1.9	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>DR</sub> = 3 A, V <sub>GS</sub> = 0 V	—	1200	—	ns
Reverse Recovery Charge	Q <sub>rr</sub>	dI <sub>DR</sub> / dt = 100 A / μs	—	8.5	—	μC

MARKING

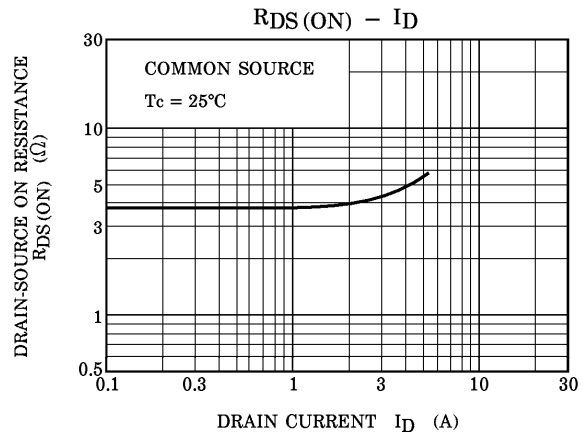
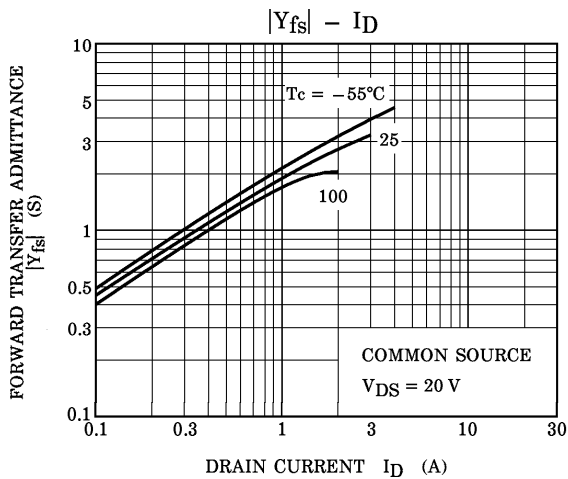
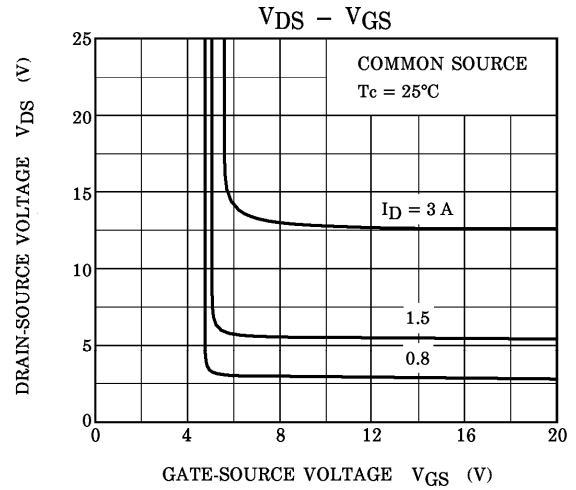
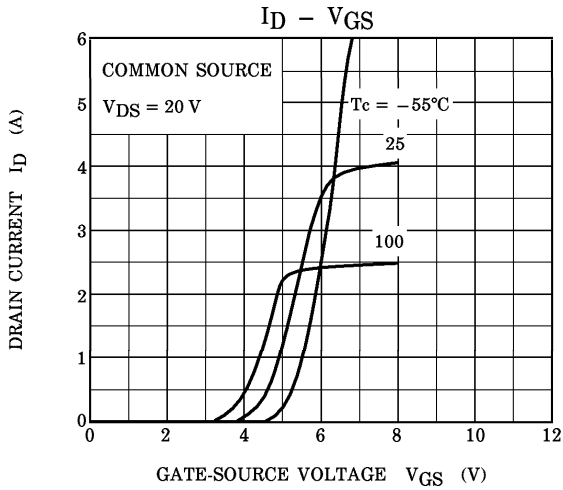
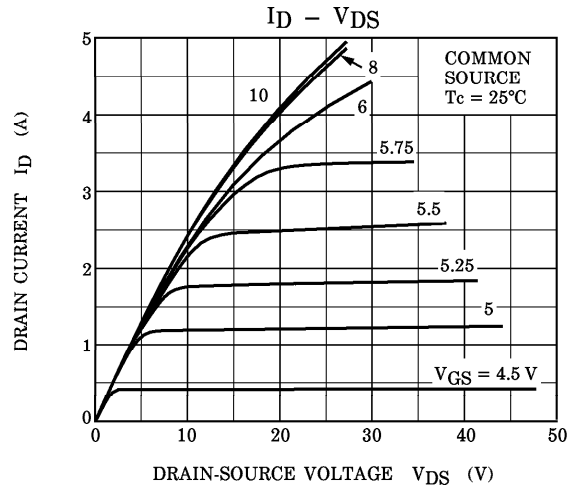
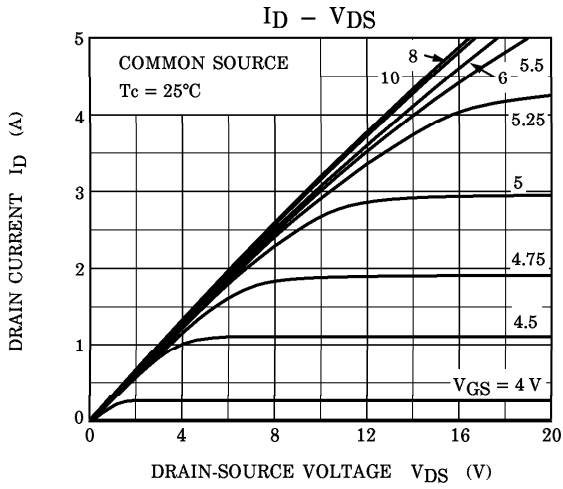


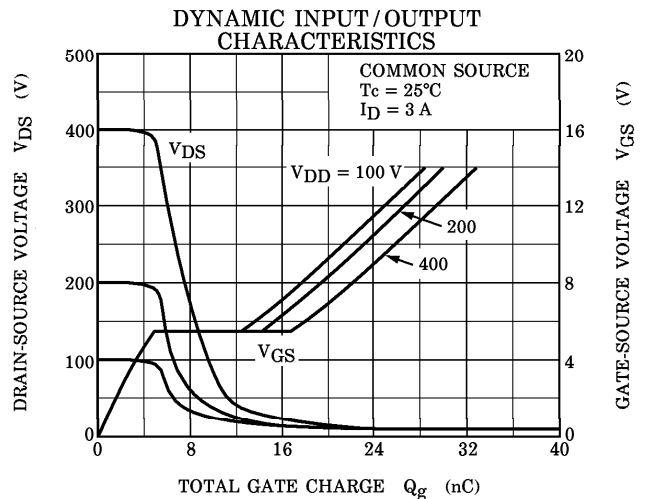
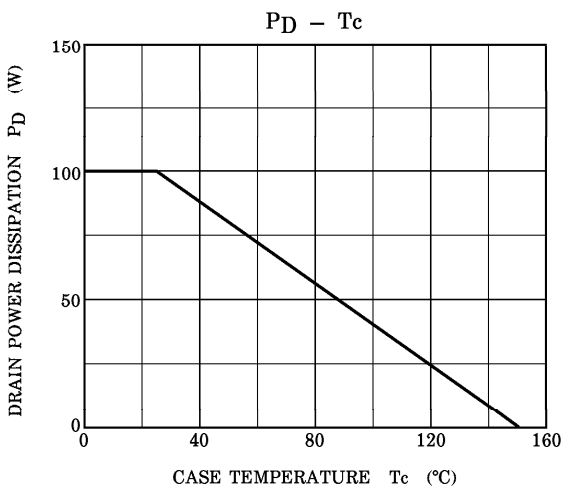
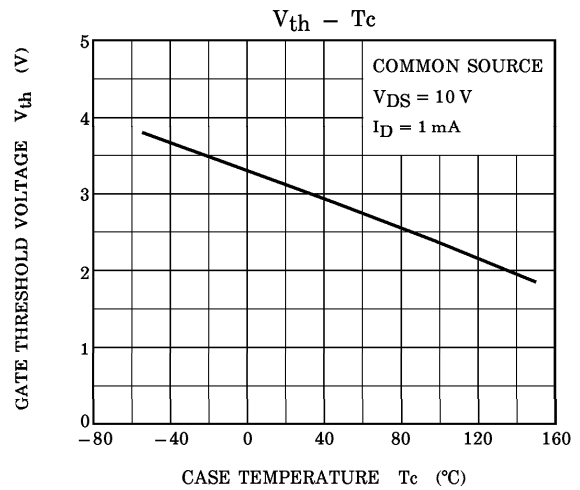
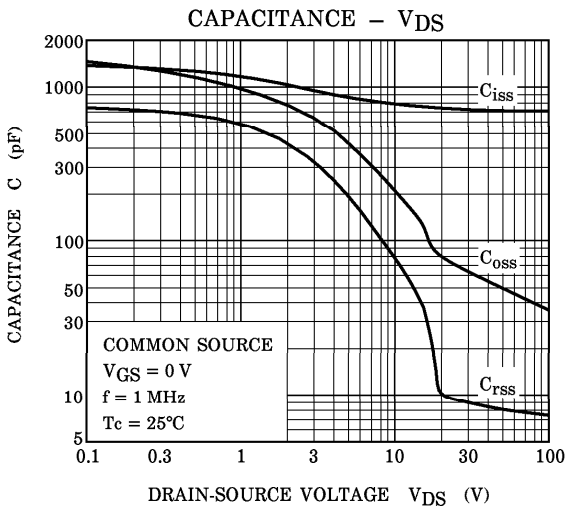
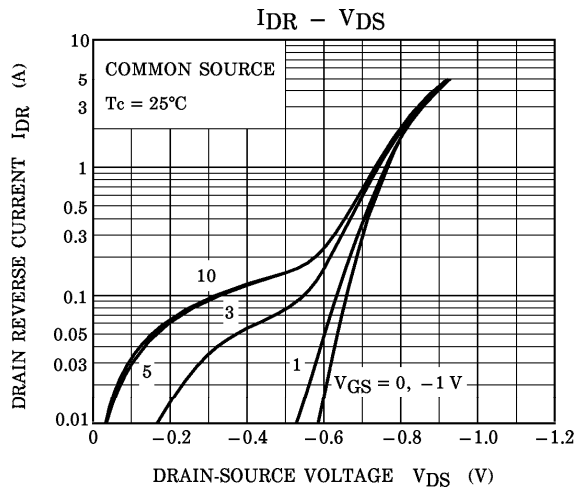
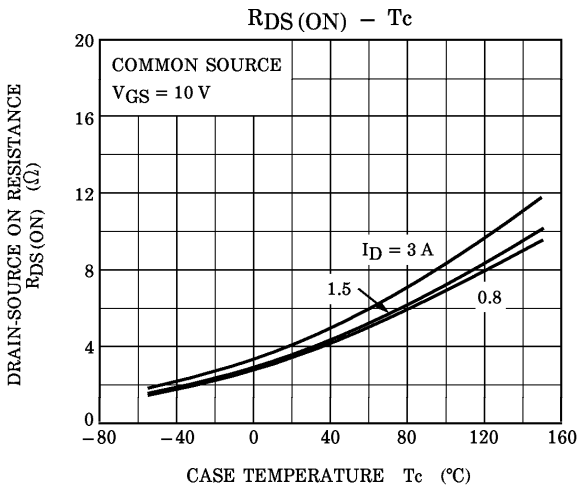
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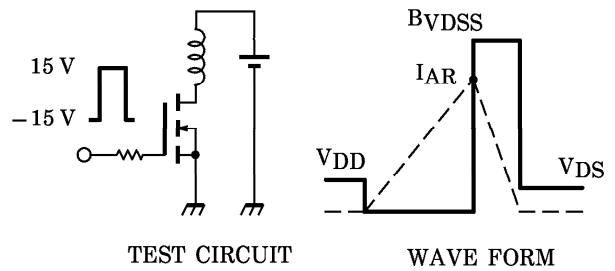
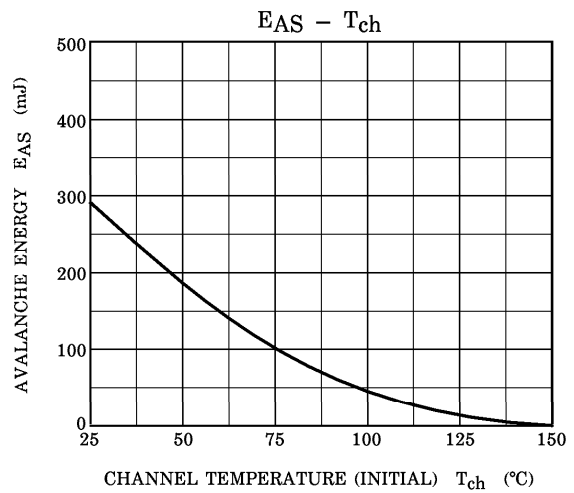
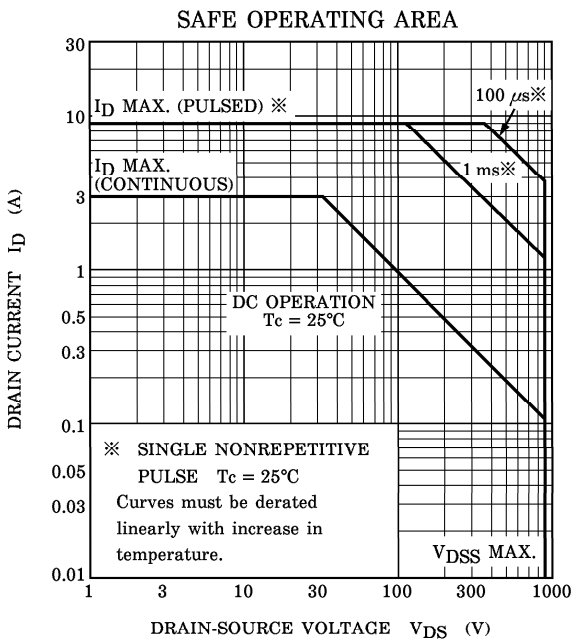
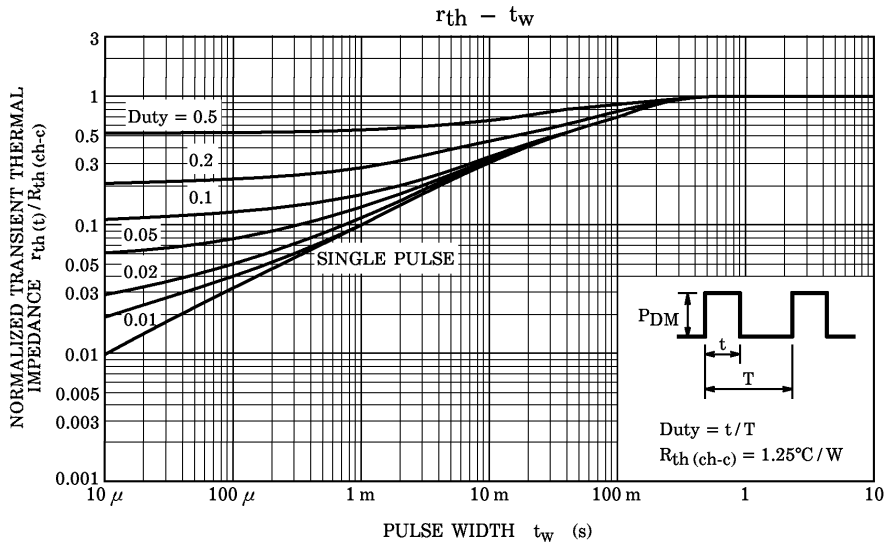
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak  $I_{AR} = 3 \text{ A}$ ,  $R_G = 25 \Omega$   
 $V_{DD} = 90 \text{ V}$ ,  $L = 60 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$